



# 60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
	$23m\Omega$ @ $V_{GS} = 10V$	55A
60V	28mΩ @ V <sub>GS</sub> = 4.5V	48A

### **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

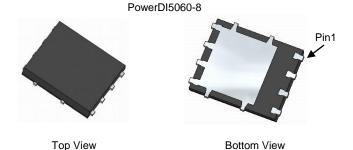
- Driving Solenoids
- Driving Relays
- Power Management Functions

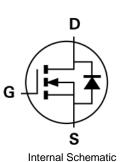
### **Features and Benefits**

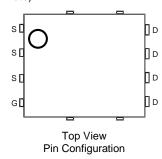
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On-State Losses
- Low Input Capacitance
- · Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Mechanical Data**

- Case: PowerDI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)







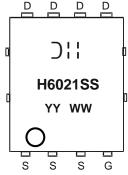
### **Ordering Information** (Note 5)

- 7			
	Part Number	Case	Packaging
	DMNH6021SPSQ-13	PowerDI5060-8	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product\_compliance\_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



);; = Manufacturer's Marking
H6021SS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 16 = 2016)
WW = Week (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



## **Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		$V_{DSS}$	60	V
Gate-Source Voltage		$V_{GSS}$	±20	V
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 8)	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I <sub>D</sub>	55 39	А
Maximum Continuous Body Diode Forward Current (Note 8)	I <sub>S</sub>	55	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	88	Α
Avalanche Current, L = 0.1mH (Note 9)		I <sub>AS</sub>	35	Α
Avalanche Energy, L = 0.1mH (Note 9)		E <sub>AS</sub>	64	mJ

### **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	$P_{D}$	1.6	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	96	°C/W
Total Power Dissipation (Note 7)	T <sub>A</sub> = +25°C	P <sub>D</sub>	3.0	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	50	°C/W
Total Power Dissipation (Note 8)	T <sub>C</sub> = +25°C	P <sub>D</sub>	53	W
Thermal Resistance, Junction to Case (Note 8)		$R_{ heta JC}$	1.5	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 10)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	-	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	1	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 10)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	-	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	D	-	12	23	mΩ	$V_{GS} = 10V, I_D = 12A$	
Static Dialii-Source Off-Resistance	R <sub>DS(ON)</sub>	-	18	28	11122	$V_{GS} = 4.5V, I_D = 12A$	
Diode Forward Voltage	V <sub>SD</sub>	-	0.75	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 11)							
Input Capacitance	C <sub>iss</sub>	-	1,016	-		$V_{DS} = 30V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Output Capacitance	Coss	-	153	-	pF		
Reverse Transfer Capacitance	$C_{rss}$	-	76.8	-			
Gate Resistance	$R_g$	-	2.5	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	-	9.5	-			
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	-	19.7	-	nC	V <sub>DS</sub> = 30V. I <sub>D</sub> = 20A	
Gate-Source Charge	$Q_{gs}$	-	3.6	-	110	VDS = 30V, ID = 20A	
Gate-Drain Charge	$Q_{gd}$	-	4.8	-			
Turn-On Delay Time	t <sub>D(ON)</sub>	-	4.2	-		$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 10A, R_{g} = 4.7\Omega$	
Turn-On Rise Time	t <sub>R</sub>	-	13	-			
Turn-Off Delay Time	t <sub>D(OFF)</sub>	=	27.5	-	ns		
Turn-Off Fall Time	t <sub>F</sub>	-	15.3	-			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	-	20.8	-	ns	1 200 4:/4+ 4000/	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	-	13.9	-	nC	$I_F = 20A$ , di/dt = 100A/ $\mu$ s	

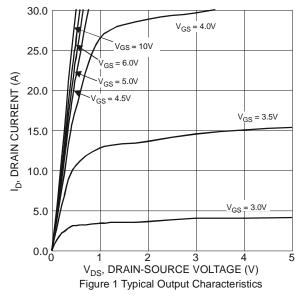
Notes:

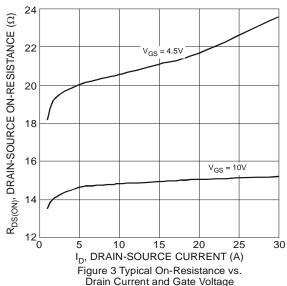
- 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- Device mounted on FR-4 PC board, with minimum recommended pad rayout, single sided.
   Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
   Thermal resistance from junction to soldering point (on the exposed drain pad).
   I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
   Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.

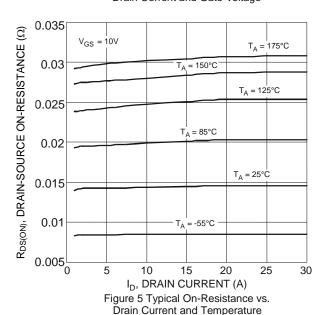
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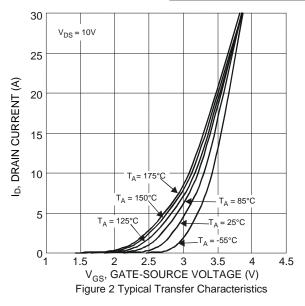


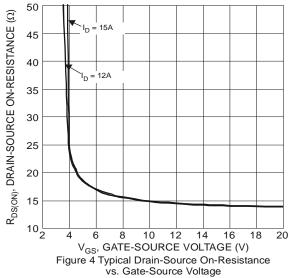


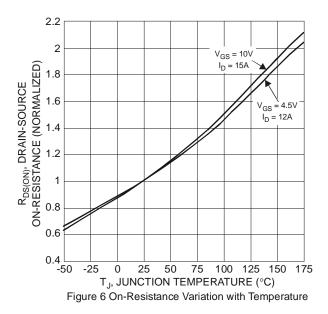








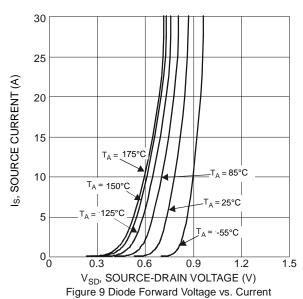


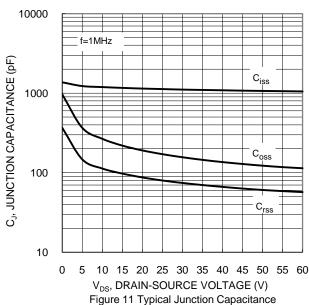


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## 0.05 R<sub>DS(ON)</sub>, DRAIN-SOURCE ON-RESISTANCE (Ω) 0.03 0.035 0.005 0.015 0.005 0.005 V<sub>GS</sub> = 4.5V I<sub>D</sub> = 12A V<sub>GS</sub> = 10V I<sub>D</sub> = 15A 75 100 125 150 175 -50 0 25 50 T<sub>.I</sub>, JUNCTION TEMPERATURE (°C) Figure 7 On-Resistance Variation with Temperature





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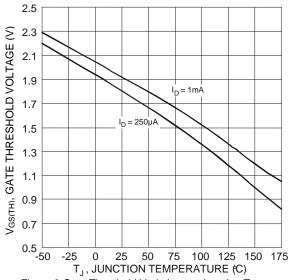
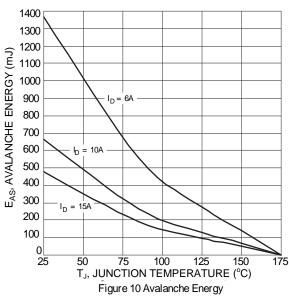
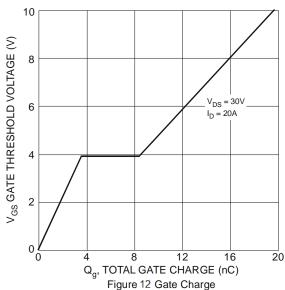


Figure 8 Gate Threshold Variation vs. Junction Temperature







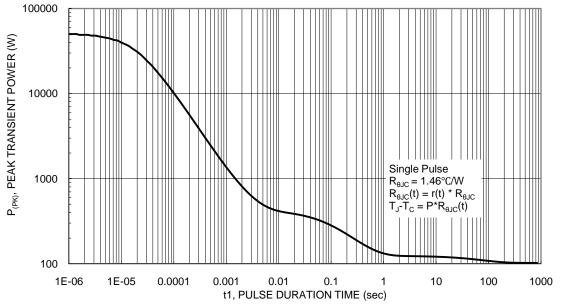
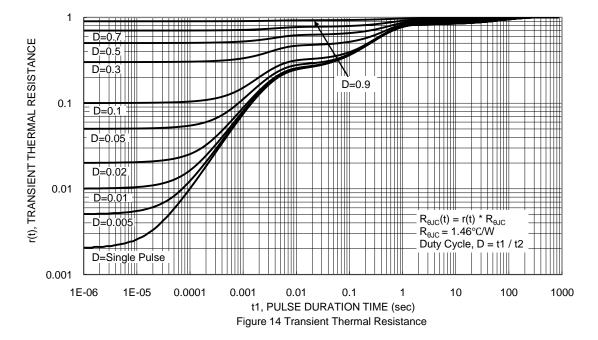


Figure 13 Single Pulse Maximum Power Dissipation

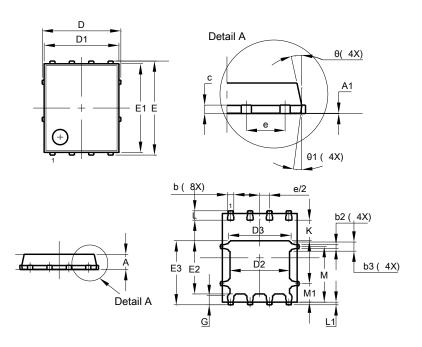




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI5060-8

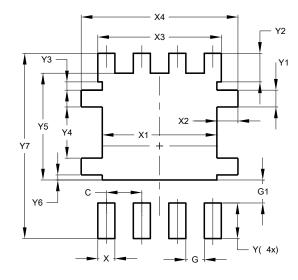


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00 0.05 -				
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D	Ļ	5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	•	6.15 BSC	;		
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	•	1.27 BSC	;		
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12º	11º		
Θ1	6º	80	7º		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI5060-8



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610



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